CLAIMS

An integrated circuit comprising:

a test circuit configured to generate a test signal having a predetermined pulse width in response to a control input, wherein said test signal tracks process corners and can be used to predict a failure of said integrated circuit.

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- 2. The integrated circuit according to claim 1, wherein said control input comprises a write enable input.
- 3. The integrated circuit according to claim 2, wherein said control input comprises a transition of a write enable input.
- 4. The integrated circuit according to claim 3, wherein said transition is from a HIGH logic level to a LOW logic level.
- 5. The integrated circuit according to claim 1, wherein said pulse width is user definable.

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- 6. The integrated circuit according to claim 5, wherein said pulse width is determined in response to one or more configuration inputs.
- 7. The integrated circuit according to claim 6, wherein said configuration inputs are fuse programmable.
- 8. The integrated circuit according to claim 6, wherein said configuration inputs are determined by a metal masking step during fabrication.
- 9. The integrated circuit according to claim 1, wherein said integrated circuit comprises a static random access memory.
- 10. The integrated circuit according to claim 9, wherein said test circuit is configured to predict a failure of one or more memory cells.

N. An integrated circuit comprising:

means for generating a test signal in response to a control input; and

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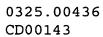
means for predicting failure of part or all of said integrated circuit in response to said test signal.

13. A method for predicting failure of an integrated circuit prior to life testing comprising the steps of:

- (A) entering a test mode;
- (B) measuring an operation of said integrated circuit in response to a test signal generated on said integrated circuit; and
 - (C) detecting failure of said operation.
- 13. The method according to claim 12, wherein said operation comprises a write operation.
- 14. The method according to claim 12, wherein said test signal is a write pulse.
- 15. The method according to claim 14, wherein said write pulse has a pulse width determined by a data setup to write end time of the integrated circuit.

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- 16. The method according to claim 12, wherein the steps (A)-(C) are performed prior to life testing.
- 17. The method according to claim 12, further comprising the step of:
- (D) sorting said integrated circuits in response to said failure.
- 18. The method according to claim 17, further comprising the step of:
 - (E) repairing said integrated circuit.
- 19. The method according to claim 12, wherein said failure comprises a poor contact in cross-coupled latch transistors of a memory cell.
- 20. The method according to claim 12, wherein step (A) comprises the sub-steps of:
 - (A-1) applying a first high voltage to an address pin of said integrated circuit;



5 (A-2) applying a second high voltage to an enable pin of said integrated circuit; and

(A-3) removing said first high voltage from said address pin.

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